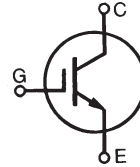


HiPerFAST™ IGBT

C2- Class High Speed IGBTs

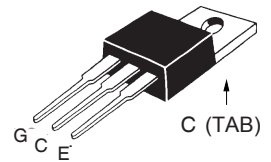
IXGP 30N60C2

$$\begin{aligned} V_{CES} &= 600 \text{ V} \\ I_{C25} &= 70 \text{ A} \\ V_{CE(sat)} &= 2.7 \text{ V} \\ t_{fi typ} &= 32 \text{ ns} \end{aligned}$$



Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C}$ to 150°C	600	V
V_{CGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GE} = 1 \text{ M}\Omega$	600	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$ (limited by leads)	70	A
I_{C110}	$T_C = 110^\circ\text{C}$	30	A
I_{CM}	$T_C = 25^\circ\text{C}$, 1 ms	150	A
SSOA (RBSOA)	$V_{GE} = 15 \text{ V}$, $T_{VJ} = 125^\circ\text{C}$, $R_G = 10 \Omega$ Clamped inductive load @ $\leq 600 \text{ V}$	$I_{CM} = 60$	A
P_C	$T_C = 25^\circ\text{C}$	190	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$
M_d	Mounting torque	1.13/10Nm/lb.in.	
Weight		4	g

TO-220 (IXGP)



G = Gate, C = Collector,
E = Emitter, TAB = Collector

Features

- Very high frequency IGBT
- Square RBSOA
- High current handling capability
- MOS Gate turn-on
- drive simplicity

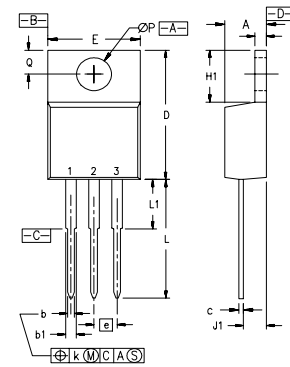
Applications

- PFC circuits
- Uninterruptible power supplies (UPS)
- Switched-mode and resonant-mode power supplies
- AC motor speed control
- DC servo and robot drives
- DC choppers

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
$V_{GE(th)}$	$I_C = 250 \mu\text{A}$, $V_{CE} = V_{GE}$	2.5		5.0 V
I_{CES}	$V_{CE} = V_{CES}$ $V_{GE} = 0 \text{ V}$ $T_J = 25^\circ\text{C}$ $T_J = 150^\circ\text{C}$			50 μA 1 mA
I_{GES}	$V_{CE} = 0 \text{ V}$, $V_{GE} = \pm 20 \text{ V}$			$\pm 100 \text{ nA}$
$V_{CE(sat)}$	$I_C = 24 \text{ A}$, $V_{GE} = 15 \text{ V}$ $T_J = 25^\circ\text{C}$			2.7 V

Symbol	Test Conditions	Characteristic Values (T _J = 25°C, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	I _C = 24 A; V _{CE} = 10 V, Pulse test, t ≤ 300 μs, duty cycle ≤ 2 %	18	28	S
C_{ies}	V _{CE} = 25 V, V _{GE} = 0 V, f = 1 MHz		1430	pF
C_{oes}			110	pF
C_{res}			40	pF
Q_g	I _C = 24 A, V _{GE} = 15 V, V _{CE} = 300 V		70	nC
Q_{ge}			10	nC
Q_{gc}			23	nC
t_{d(on)}	Inductive load, T _J = 25°C I _C = 24 A, V _{GE} = 15 V V _{CE} = 400 V, R _G = 5 Ω		13	ns
t_{ri}			15	ns
t_{d(off)}			70	ns
t_{fi}			60	ns
E_{off}			0.19	mJ
t_{d(on)}	Inductive load, T _J = 125°C I _C = 24 A, V _{GE} = 15 V V _{CE} = 400 V, R _G = 5 Ω		13	ns
t_{ri}			17	ns
E_{on}			0.22	mJ
t_{d(off)}			120	ns
t_{fi}			130	ns
E_{off}			0.59	mJ
R_{thJC}				0.65 K/W
R_{thCH}			0.25	K/W

TO-220 Outline



Pins: 1 - Gate 2 - Drain
3 - Source 4 - Drain

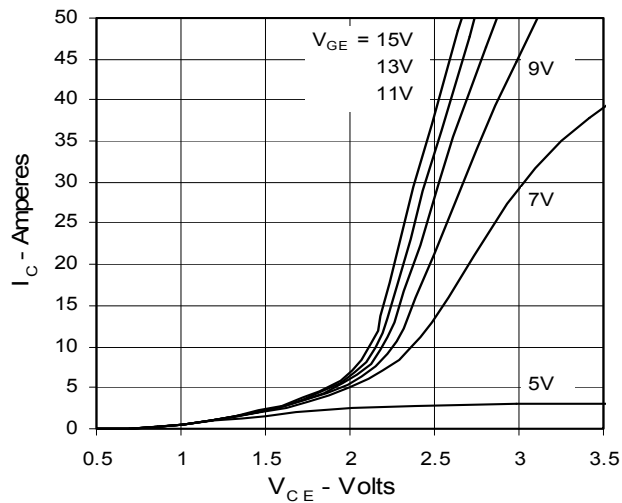
SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b1	.045	.065	1.15	1.65
c	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
e	.100	BSC	2.54	BSC
F	.045	.055	1.14	1.40
H1	.230	.270	5.85	6.85
J1	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L1	.110	.230	2.79	5.84
Q	.139	.161	3.53	4.08
Q	.100	.125	2.54	3.18

IXYS reserves the right to change limits, test conditions, and dimensions.

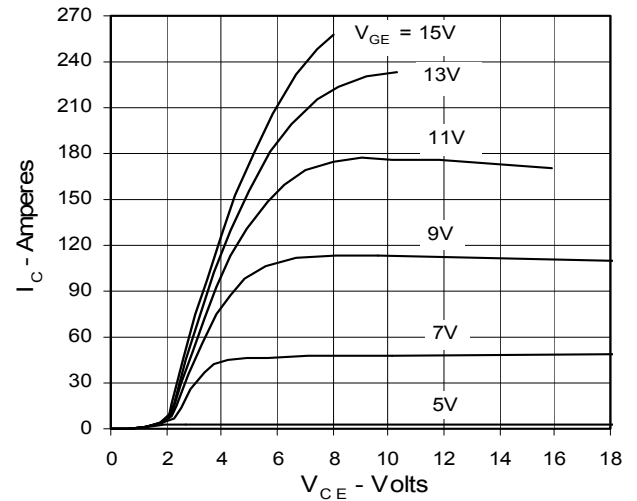
IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585
4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2

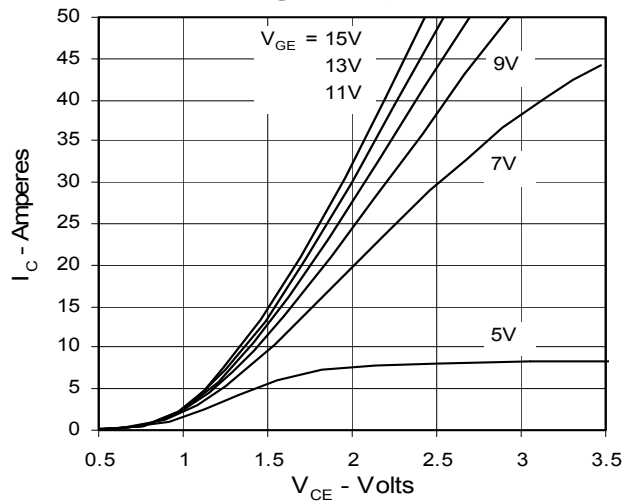
**Fig. 1. Output Characteristics
@ 25 Deg. C**



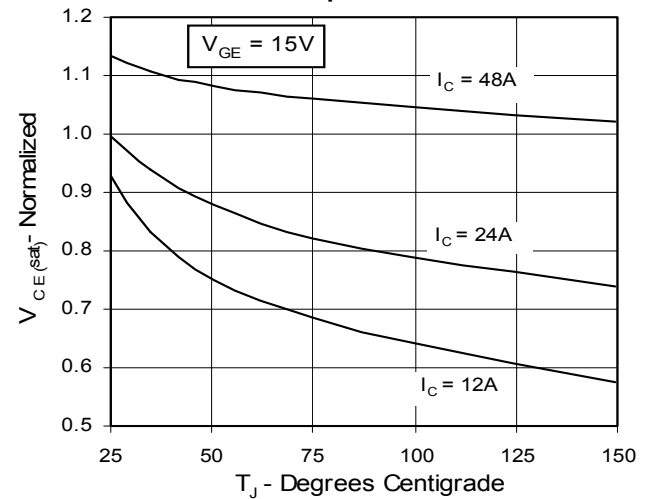
**Fig. 2. Extended Output Characteristics
@ 25 deg. C**



**Fig. 3. Output Characteristics
@ 125 Deg. C**



**Fig. 4. Dependence of $V_{CE(sat)}$ on
Temperature**



**Fig. 5. Collector-to-Emitter Voltage
vs. Gate-to-Emitter voltage**

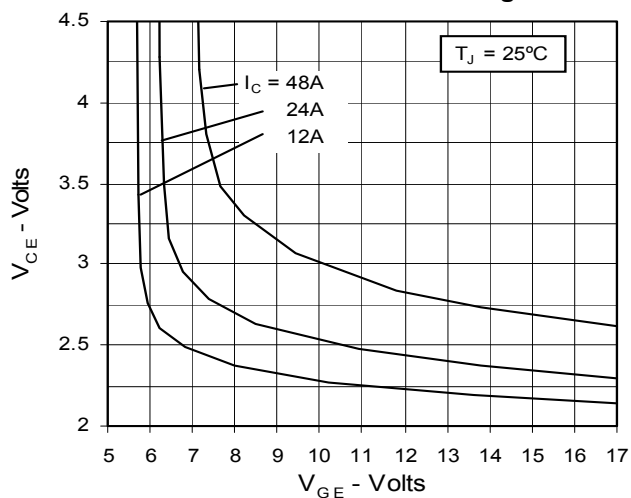


Fig. 6. Input Admittance

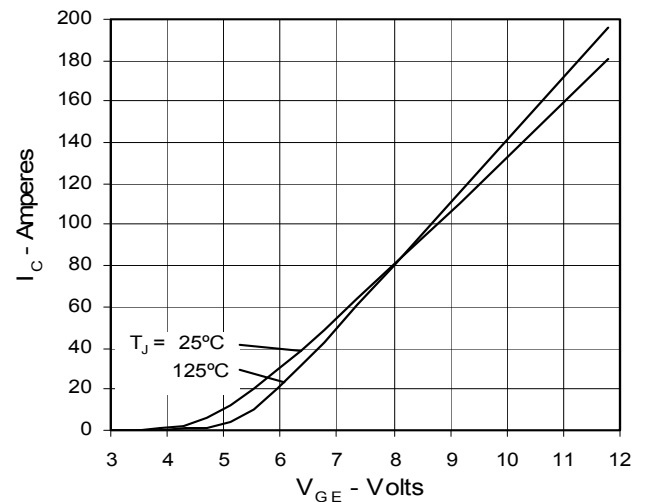


Fig. 7. Transconductance

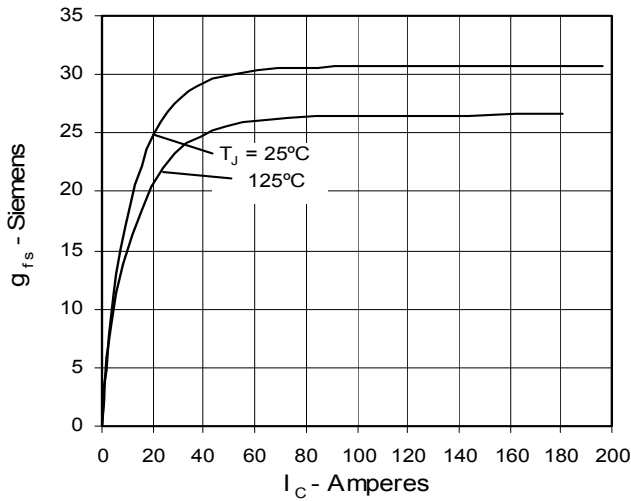
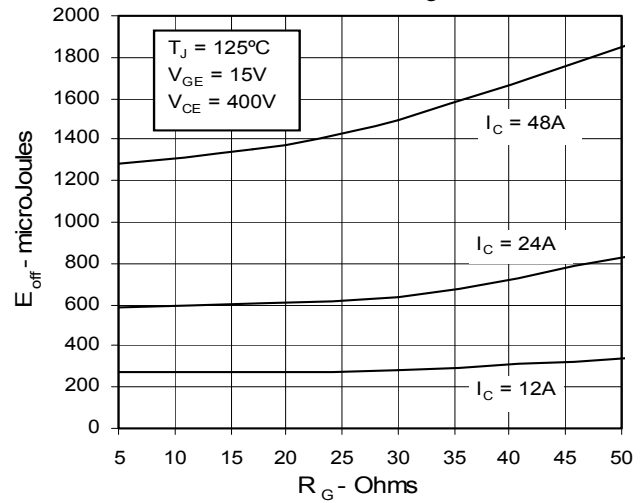
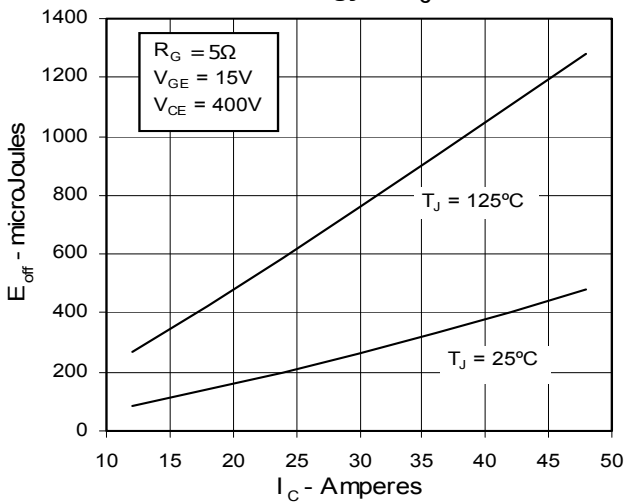

Fig. 8. Dependence of Turn-Off Energy on R_G

Fig. 9. Dependence of Turn-Off Energy on I_C


Fig. 10. Dependence of Turn-Off Energy on Temperature

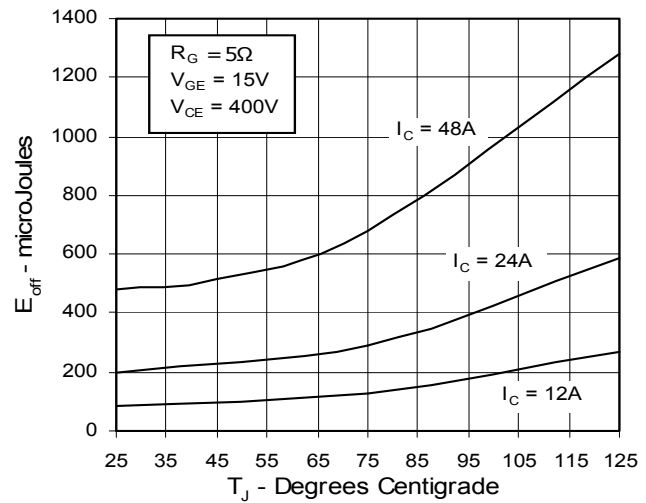
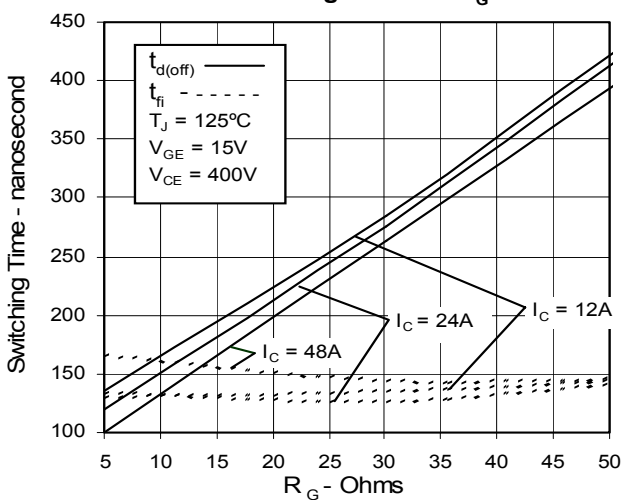
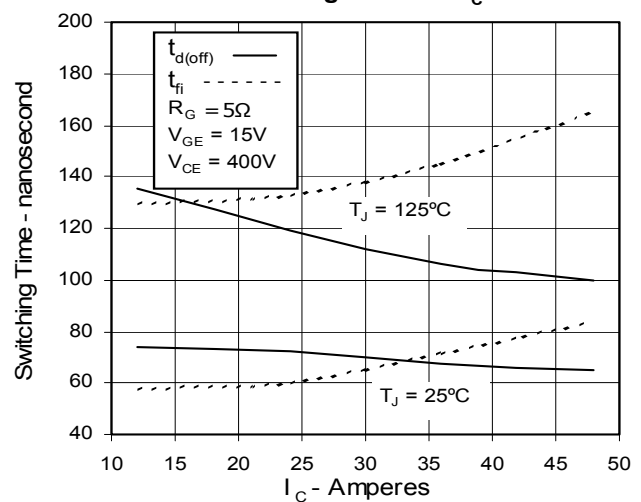

Fig. 11. Dependence of Turn-Off Switching Time on R_G

Fig. 12. Dependence of Turn-Off Switching Time on I_C


Fig. 13. Dependence of Turn-Off Switching Time on Temperature

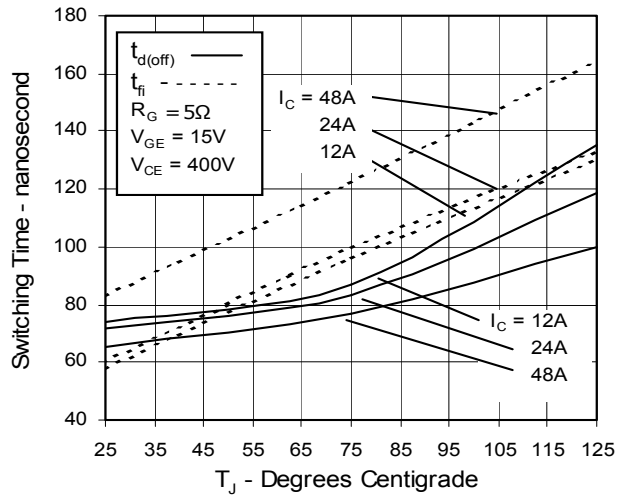


Fig. 14. Gate Charge

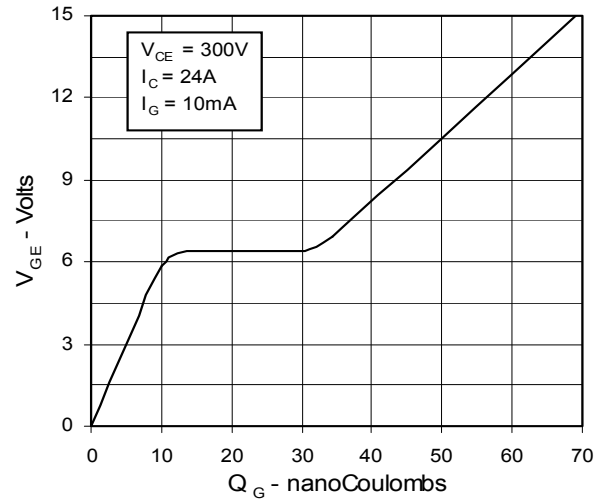


Fig. 15. Capacitance

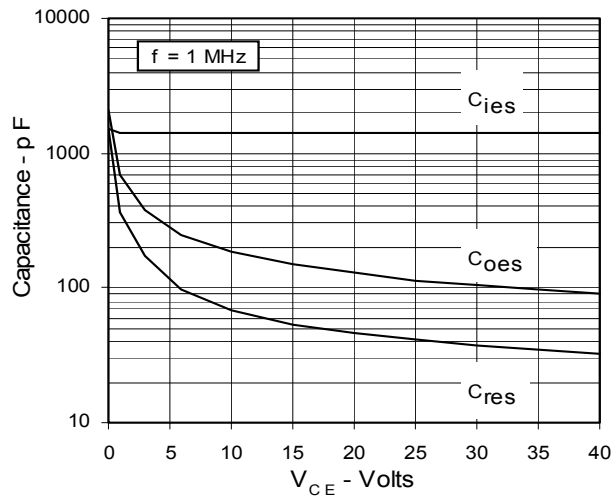


Fig. 16. Maximum Transient Thermal Resistance

